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Form PTO-1449

For:

Applicant: Ryuzo Iga et al. Serial No.: 10/577,626 Filing Date: April 28, 2006

Sheet 1 of 2 Confirmation No.: 9935 Att'y Docket No.: 14321.84 Art Unit: 2828 SEMICONDUCTOR OPTICAL DEVICE AND A METHOD OF FABRICATING THE SAME

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

Examiner <u>Initial*</u>	Document Number	Issue <u>Date</u>	Name
1	5,470,785	11/28/1995	Kondo
2	6,300,153 B1	10/09/2001	Koui
3	2001/0030327 A1	10/18/2001	Furushima
4	2003/0067010 A1	04/10/2003	Iga et al.
5	2004/0057483 A1	03/25/2004	Takemi et al.

Foreign Patent Documents

Examiner <u>Initial</u> *	Document Number	Publication	Country or Patent Office	Translation
6	61-180493	08/13/1986	Japan	Partial
7	3-53582	03/07/1991	Japan	Partial
8	05-021891	01/29/1993	Japan	No
9	05-102607	04/23/1993	Japan	No
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12	07-162091	06/23/1995	Japan	No
13	07-202317	08/04/1995	Japan	No
14	09-283846	10/31/1997	Japan	No
15	2000-260714	09/22/2000	Japan	No
16	2001-298240	01/26/2001	Japan	No
17	2003-60311	02/28/2003	Japan	No
18	2004-119467	04/15/2004	Japan	No
Examiner:	/Patrick Stafford/	Date Consi	dered: 07/08/2008	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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 Sheet 2 of 2

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Filing Date: SEMICONDUCTOR OPTICAL DEVICE AND A METHOD OF FABRICATING THE SAME For: Other Documents (including author, title, pertinent pages, etc.) Examiner Initial* A. Dadgar et al., Ruthenium: A Superior Compensator of InP. Applied Physics Letters, Vol. 73. 19 No. 26. December 28, 1998, pp. 3878-3880. A. van Geelen et al., Ruthenium Doped High Power 1.48 um SIPBH Laser, 11th International 20 Conference on Indium Phosphide and Related Materials, Davos, Switzerland, May 16-20, 1999. TuB 1-2, pp. 203-206. 21 Ryuzo Iga et al., Ruthenium-Doped InP Buried 1.3 µm DFB Lasers on a P-Type Substrate, 2004 International Conference on Indium Phoshide and Related Materials, Conference Proceedings, 16th IPRM, Kagoshima, Japan, May 31-June 4, 2004, pp. 742-745. 22 Ryuzo Iga et al., Directly Modulated 1.3 µm DFB Lasers with a Buried Heterostructure Using Ru-doped Semi-Insulating InP, Technical Report of IEICE, EMD2004-43, CPM2004-69, OPE2004-126, LQE2004-41(2004-08), pp. 19-24 (only Abstract is attached). 23 Rvuzo Iga et al., Directly Modulated 1.3-um DFB Laser with a Buried Structure Formed by Using Ru-doped Semi-insulating InP, 31p-ZH-10, 2005 (all the document is translated).

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While the filing of Information Disclosure Statements is voluntary, the procedure is governed by the guidelines of Section 609 of the Manual of Patent Examining Procedure and 37 C.F.R. §§ 1.97 and 1.98. To be considered a proper Information Disclosure Statement, Form PTO-1449 shall be accompanied by a copy of each listed patent or publication or other item of information and a translation of the pertinent portions of foreign documents (if an existing translation is readily available to the applicant), an explanation of relevance of each reference not in the English language, and should be submitted in a timely manner as set out in MPEP Sec. 609.

Examiners will consider all citations submitted in conformance with 37 C.F.R. § 1.98 and MPEP Sec. 609 and place their initials adjacent the citations in the spaces provided on this form. Examiners will also initial citations not in conformance with the guidelines which may have been considered. A reference may be considered by the Examiner for any reason whether or not the citation is in full conformance with the guidelines. A line will be drawn through a citation if it is not in conformance with the guidelines AND has not been considered. A copy of the submitted form, as reviewed by the Examiner, will be returned to the applicant with the next communication. The original of the form will be entered into the application file.

Each citation initialed by the Examiner will be printed on the issued patent in the same manner as references cited by the Examiner on Form PTO-892.

The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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Examiner:

/Patrick Stafford/

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Date Considered:

07/08/2008